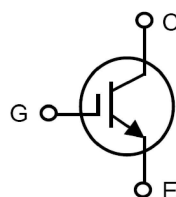


# XPT™ 650V GenX5™ IGBT

## IXYH120N65A5

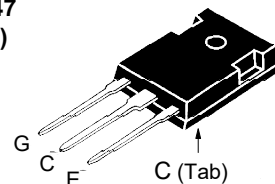
Extreme Light Punch Through  
IGBT for up to 10kHz Switching



$V_{CES} = 650V$   
 $I_{C110} = 120A$   
 $V_{CE(sat)} \leq 1.35V$   
 $t_{fi(typ)} = 160ns$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	650	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	650	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$ (Chip Capability)	290	A
$I_{LRMS}$	Terminal Current Limit	160	A
$I_{C110}$	$T_C = 110^\circ C$	120	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	790	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 3\Omega$ Clamped Inductive Load	$I_{CM} = 240$ $V_{CE} \leq V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	830	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ C$
$M_d$	Mounting Torque	1.13 / 10	Nm/lb.in
<b>Weight</b>		6	g

TO-247  
(IXYH)



G = Gate      C = Collector  
E = Emitter    Tab = Collector

### Features

- Optimized for Low Frequency High Current Switching
- High Surge Current Capability
- Square RBSOA
- International Standard Package

### Advantages

- High Power Density
- Low Gate Drive Requirement

### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.7		5.8 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			5 $\mu A$ 750 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 75A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$	1.22 1.30		1.35 V V

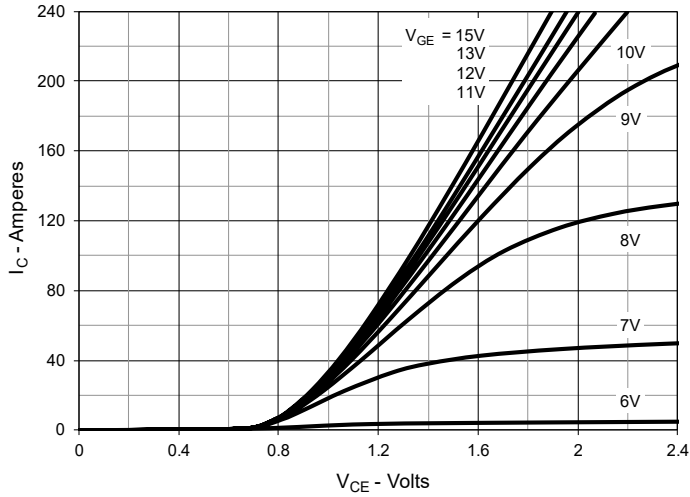
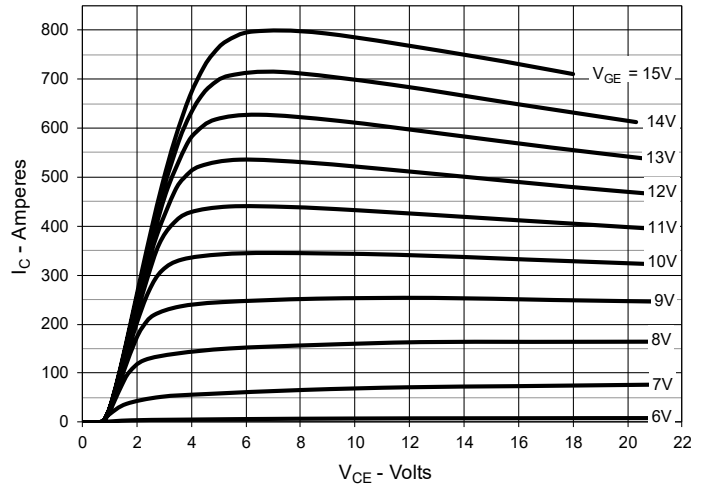
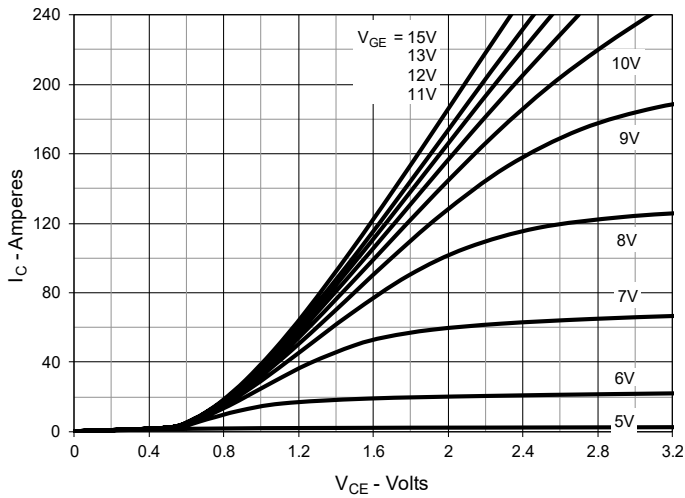
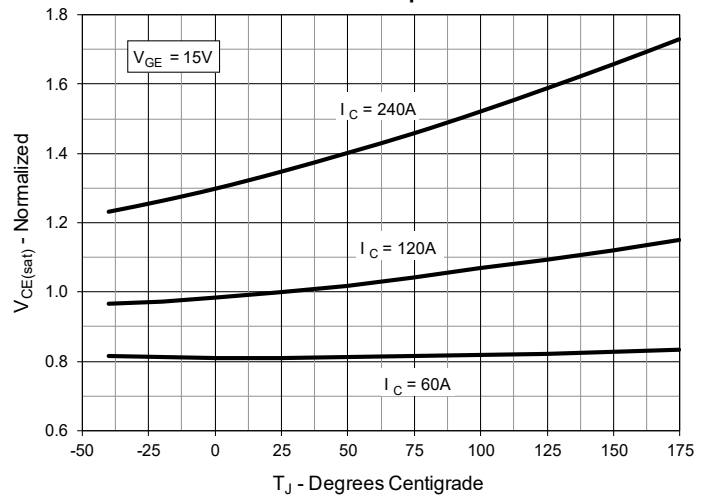
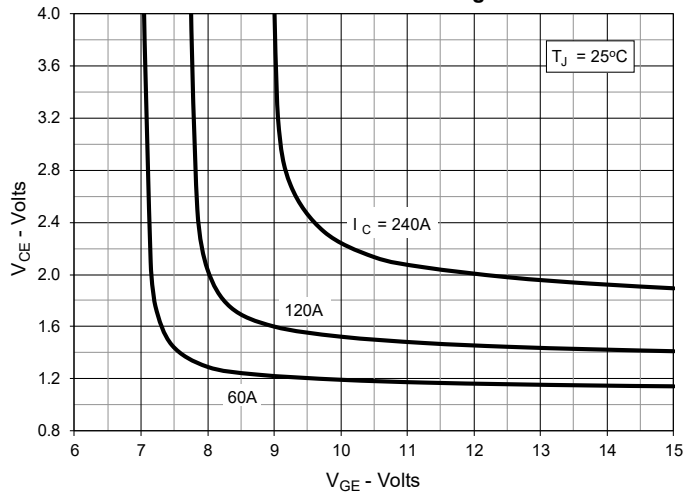
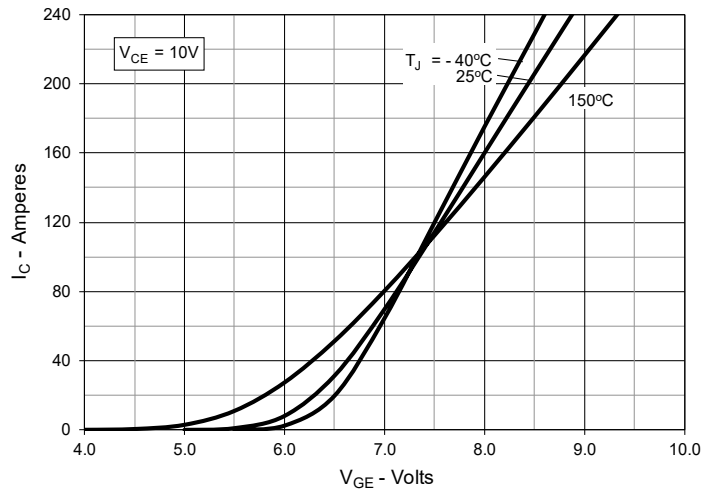
Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
	Min.	Typ.	Max.
$g_{fs}$ $I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	48	80	S
$C_{ies}$ $C_{oes}$ $C_{res}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	5060	pF
		255	pF
		190	pF
$Q_{g(on)}$ $Q_{ge}$ $Q_{gc}$	$I_C = 90\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$	314	nC
		41	nC
		157	nC
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 60\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 3\Omega$ Note 2	45	ns
		42	ns
		1.25	mJ
		370	ns
		160	ns
		3.20	mJ
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 60\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 3\Omega$ Note 2	33	ns
		42	ns
		2.30	mJ
		360	ns
		290	ns
		4.70	mJ
$R_{thJC}$			0.18 $^\circ\text{C/W}$
$R_{thCS}$	0.21		$^\circ\text{C/W}$

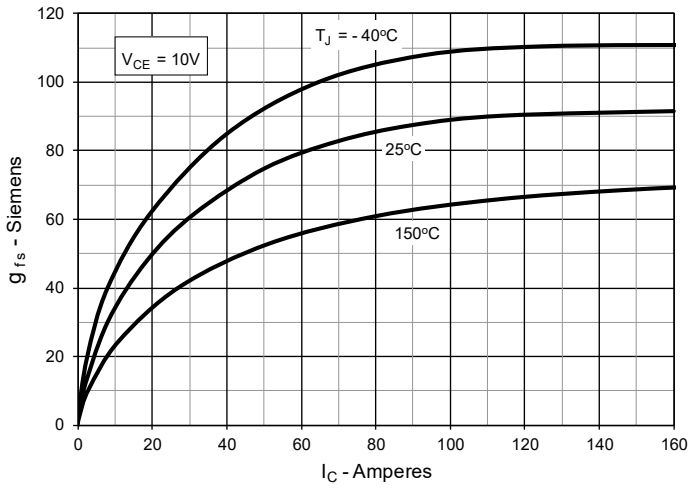
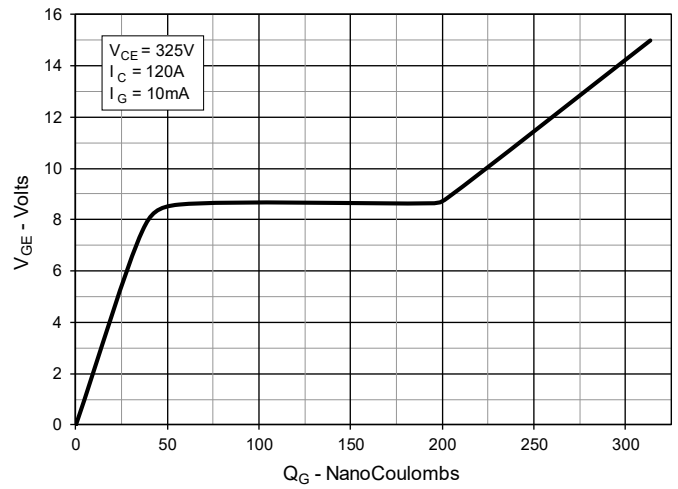
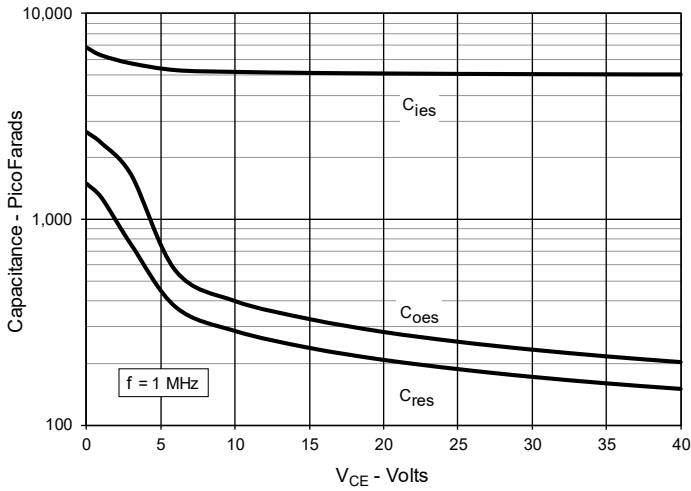
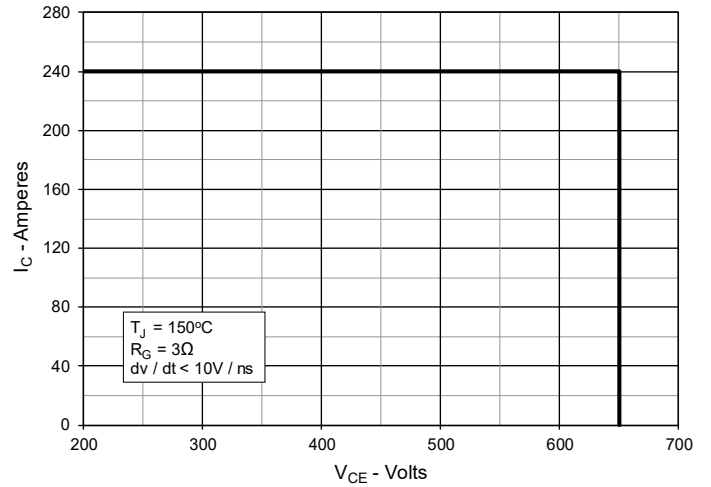
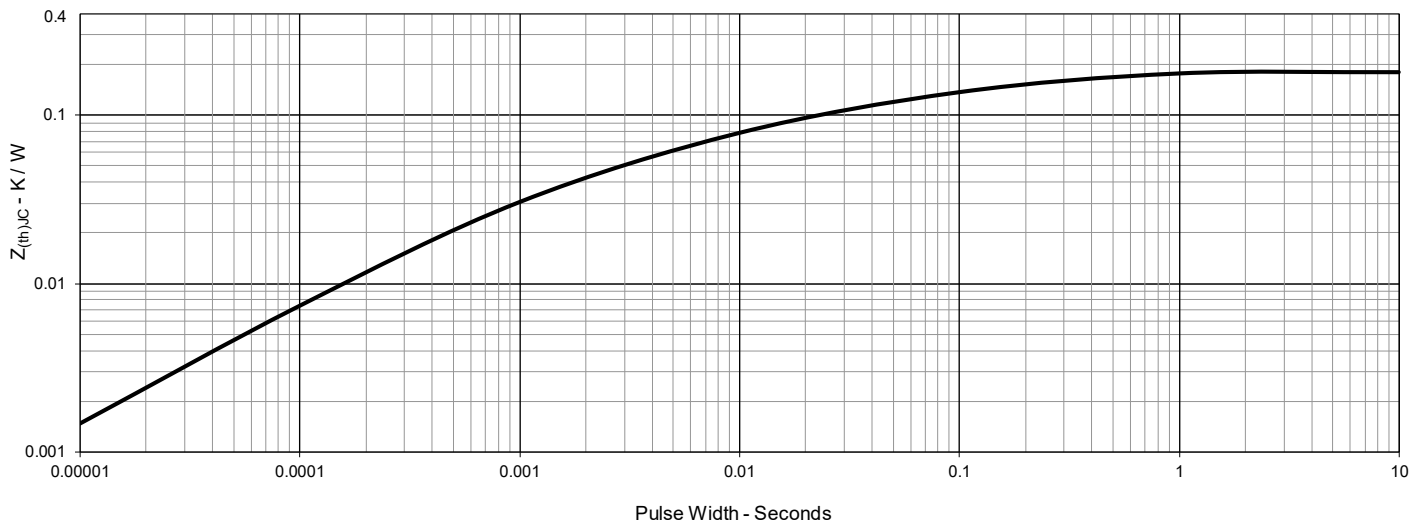
**Notes:**

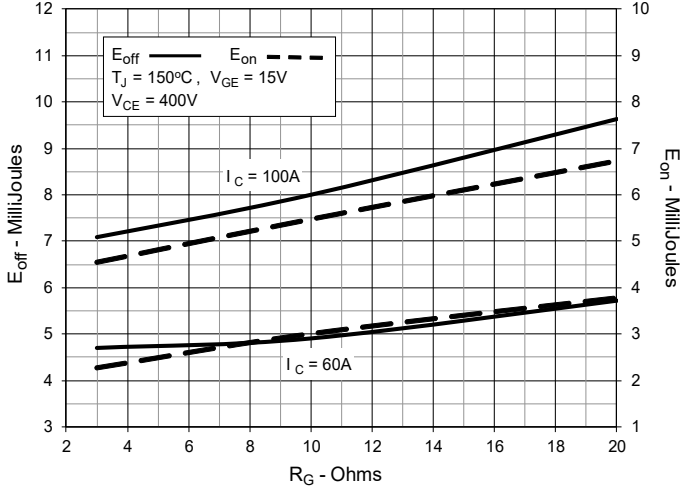
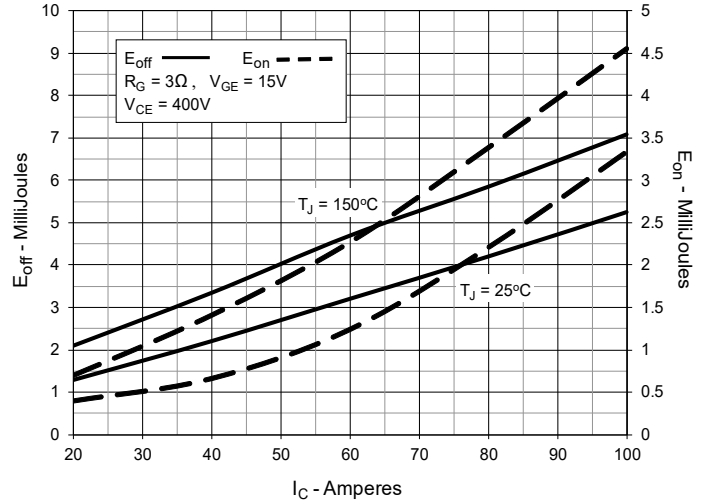
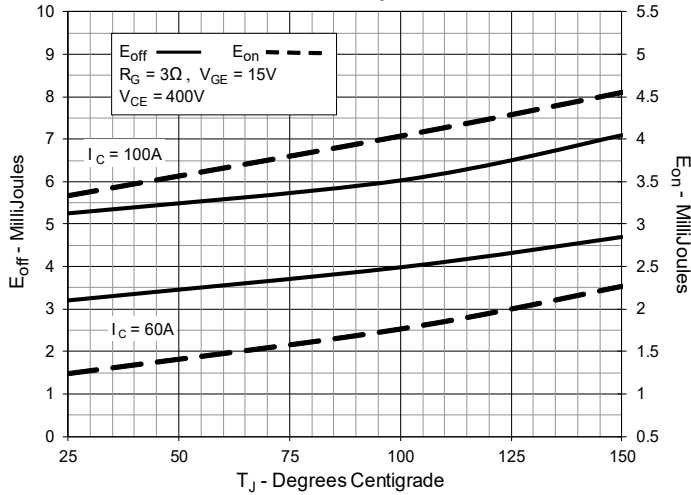
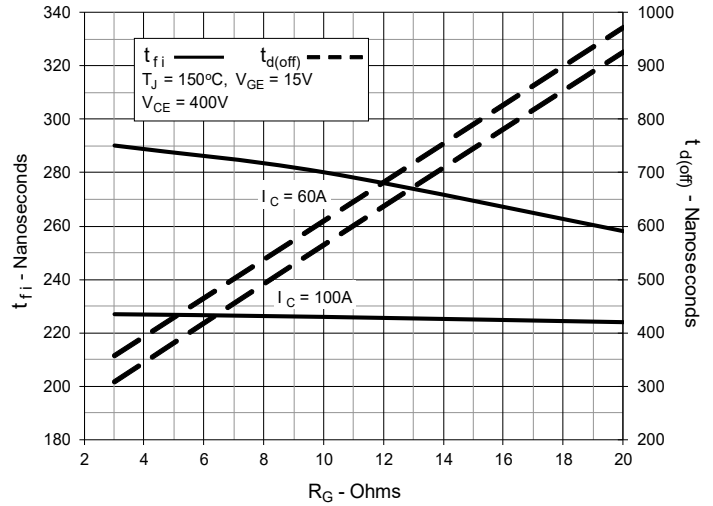
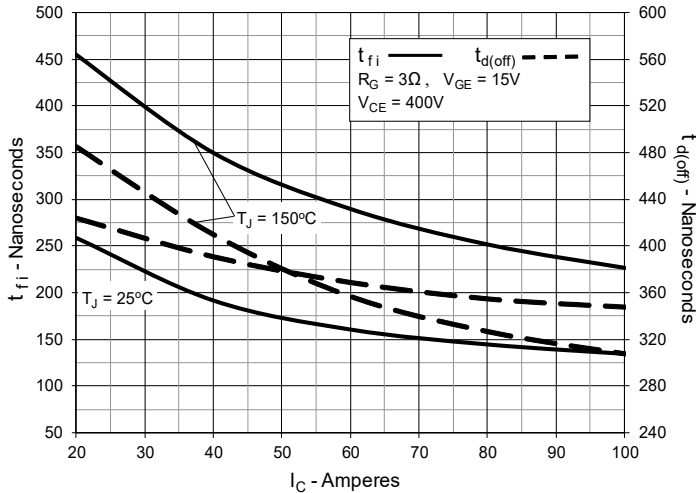
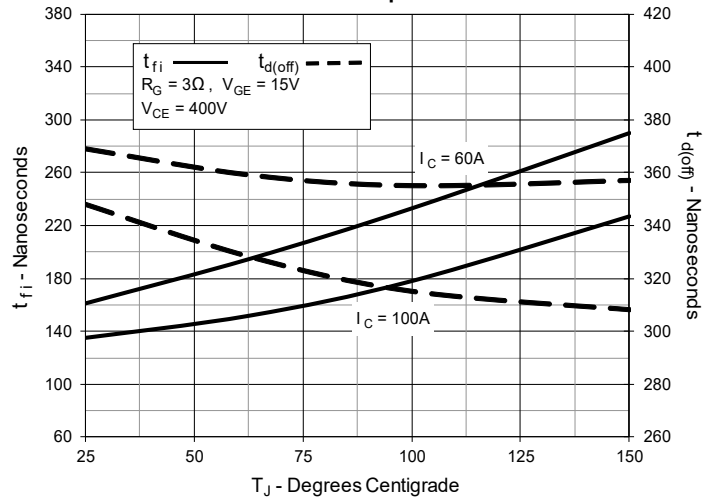
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (clamp),  $T_J$  or  $R_G$ .

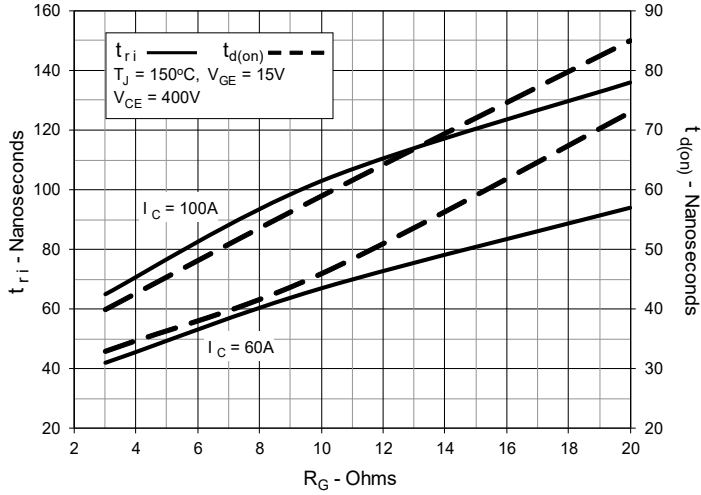
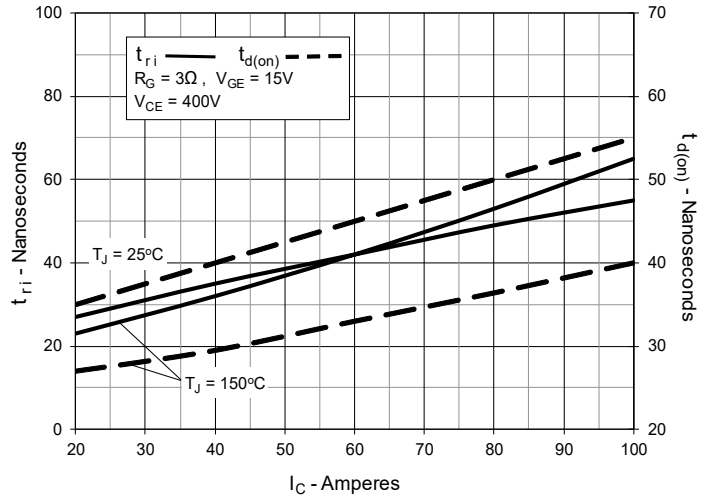
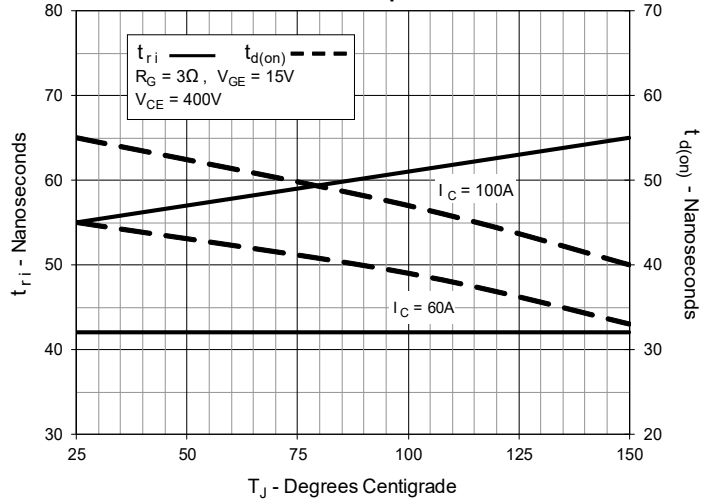
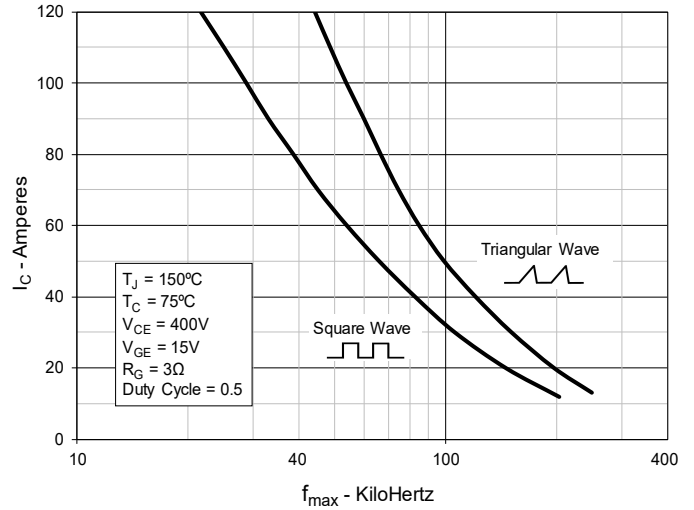
Littelfuse reserves the right to change limits, test conditions, and dimensions.

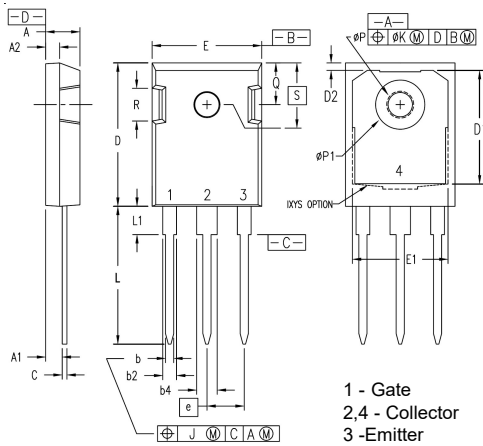
IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or more of the following U.S. patents:	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$** 

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


**Fig. 7. Transconductance**

**Fig. 8. Gate Charge**

**Fig. 9. Capacitance**

**Fig. 10. Reverse-Bias Safe Operating Area**

**Fig. 11. Maximum Transient Thermal Impedance**


**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**

**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**

**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**

**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**

**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**

**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**


**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**

**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**

**Fig. 21. Maximum Peak Load Current vs. Frequency**


**TO-247 Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	